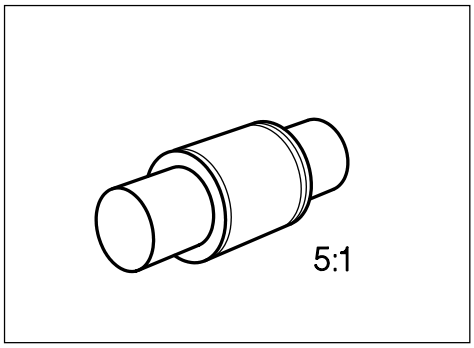
SIEMENS

Silicon Tuning Varactor

BBY 33 BB-2

- Tuning varactor in passivated Mesa technology (epitaxial design)



Type	Marking	Ordering Code	Pin Configuration	Package[1)]
BBY 33 BB-2	–	Q62702-B70	Cathode: black dot, heat sink 	C 1

Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	V_R	27	V
Forward current	I_F	200	mA
Junction temperature	T_j	175	°C
Storage temperature range	T_{stg}	– 55 … + 150	
Operating temperature range	T_{op}	– 55 … + 150	

1) For detailed information see chapter Package Outlines.

Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward voltage I_F = 200 mA	V_F	–	–	1.1	V
Reverse current V_R = 15 V	I_R	–	–	5	nA
Diode capacitance V_R = 0	C_T	0.9	–	1.5	pF
Capacitance ratio V_R = 0, V_R = 25 V	$\frac{C_{T0}}{C_{T25}}$	–	3.0	–	–
Figure of merit V_R = 4 V, f = 50 MHz	$Q_{(min)}$	4000	–	–	–